ECE1371 Advanced Analog Circuits

MATCHING AND MISMATCH SHAPING

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Highlights (i.e. What you will learn today)

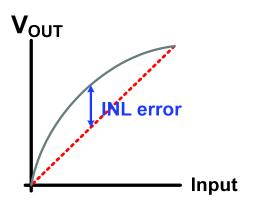
- 1. Sources of Mismatch
- 2. Some matching techniques
 Common-centroid
 Interdigitation
- 3. Mismatch Shaping
 Randomization, 1st and 2nd order schemes

Need for Matching

 Poorly matched devices (transistors, capacitors, resistors) can lead to non-idealities

Amplifier Offset
Converter Non-linearity
Gain Error

DAC mismatch in ΔΣ
 Mismatch in DAC current sources or capacitors causes INL error in output



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Sources of Matching Error

- Systematic Mismatch
 Introduced by circuit/layout designer
 Can usually be avoided
- Random Mismatch

Variation in process parameters and lithography
Beyond the designers control – must take these into
account during the design process

Gradient Mismatch

First- or second-order fluctuations over longer lengths across the chip

Systematic Mismatch

 Some good design techniques exist to help minimize these matching errors

Use multiples of small, unit sized devices (transistor stripes, resistor and capacitor arrays)

Use cascodes – increased output impedence (smaller current variations with changes in V_{DS})

Avoid asymmetric loading – especially for dynamic signals (match wire lengths, capacitances)

Don't mix different types of devices if they are supposed to match (e.g., poly resistors and n+resistors)

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Random Mismatch

Due to random variations in...

Device length

Channel doping

Oxide thickness

Sheet resistance

Capacitance

How are these errors reduced?

Increased device area

Increased Area/Perimeter ratio (square is best)

(more on this later...)

Gradient Mismatch

 To avoid these errors, devices should have similar environment

Same size, orientation, location, supplies, temperature

Minimize these errors with some layout techniques

Common-centroid – when devices are supposed to be matched, balance them so that their centroids are the same (eliminates 1st-order gradient errors)

Interdigitation – not strictly common-centroid, but reduces impact of gradient errors

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Capacitor Matching

Example: Matching two capacitors C₁ and C₂

C₁ is 3pF

C₂ is 4pF

Want to maintain the 3:4 relative size with minimal errors

How do we layout these capacitors?

Consider over-etching errors

Capacitance

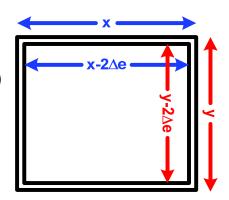
$$C = xyC_{ox}$$

Capacitance error (for small Δe)

$$\Delta C \approx -2\Delta e(x+y)C_{ox}$$

Relative error

$$\varepsilon_r = \frac{\Delta \mathbf{C}}{\mathbf{C}} \approx -2\Delta \mathbf{e} \frac{\mathbf{x} + \mathbf{y}}{\mathbf{x} \mathbf{y}}$$



For a given area, relative capacitance error is minimized for x=y (square)

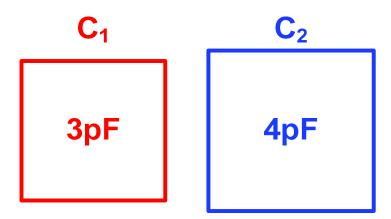
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Capacitor Matching Example

Option 1

Make C_1 and C_2 both square capacitors with capacitor C_2 33% times bigger than C_1

=> minimizes relative capacitor error



 How do we preserve the 3:4 ratio with a given relative error for each?

$$\frac{C_1}{C_2} \approx \frac{3(1 + \varepsilon_{r,3pF})}{4(1 + \varepsilon_{r,4pF})}$$

$$\varepsilon_{r,3pF} = \frac{\Delta C}{C} \approx -2\Delta e \frac{X_{3pF} + Y_{3pF}}{X_{3pF}Y_{3pF}}$$

$$\varepsilon_{r,4pF} = \frac{\Delta C}{C} \approx -2\Delta e \frac{X_{4pF} + Y_{4pF}}{X_{4pF}Y_{4pF}}$$

Ratio will be 3:4 as long as

$$\frac{\mathbf{X}_{3pF} + \mathbf{y}_{3pF}}{\mathbf{X}_{3pF} \mathbf{y}_{3pF}} = \frac{\mathbf{X}_{4pF} + \mathbf{y}_{4pF}}{\mathbf{X}_{4pF} \mathbf{y}_{4pF}}$$

Keep the area to perimeter ratio the same for both capacitors

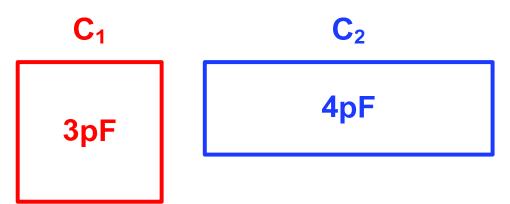
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Capacitor Matching Example

Option 2

Make C₂ 33% larger than C₁ but with the same area to perimeter ratio

=> matches relative capacitor error



How do we match the boundary of each capacitor?

With irregularly shaped capacitors it is difficult to ensure that every capacitor 'sees' the same edges/materials

 Unit-sized capacitors with surrounding dummy capacitors

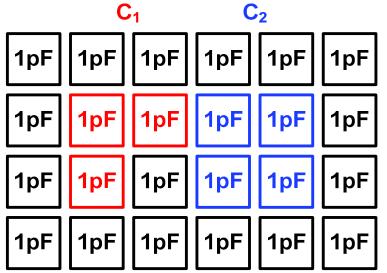
Smaller unit-sized capacitors can be realized to ensure that every capacitor 'sees' the same surrounding area

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Capacitor Matching Example

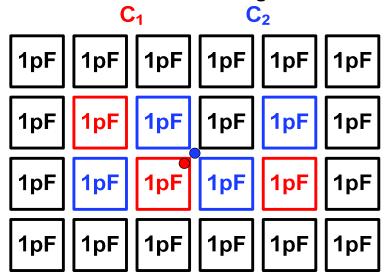
Option 3

Divide into unit-sized 1pF capacitors
Use dummy capacitors around main C₁ and C₂



Option 4

Common-centroid layout (with dummy caps)
Minimizes effects of 1st-order gradients

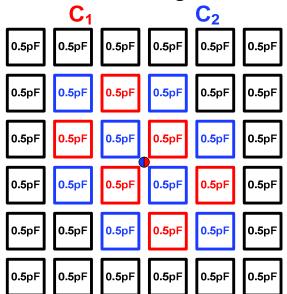


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Capacitor Matching Example

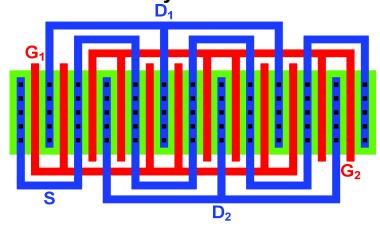
Option 5

Smaller unit-sized capacitors (with dummy caps)
Centroids can be closer together or identical



Interdigitation

Simple way to reduce 1st-order gradient effects Easiest when MOS devices have same source node Useful for current mirrors and differential pairs As the number of fingers increases, this approaches a common-centroid layout



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Reducing Random Mismatch

Even with interdigitation or common-centroid, random mismatch will exist in a diff. pair

Mismatch is proportional to area of transistor Standard deviation of error is

$$\sigma_{\Delta VT} = \frac{A_{VT}}{\sqrt{WL}}$$

 A_{VT} decreases almost linearly with each process generation (proportional to oxide thickness)

Drain current variation

 $\frac{\sigma_I}{I}\bigg|_{VT} = \sigma_{VT} \frac{2}{V_{00} - V_T} = \frac{A_{VT}}{\sqrt{WL}} \frac{2}{(V_{00} - V_T)}$

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What happens when...?

...the device current is decreased by 4x?

Error current $g_m \Delta V_T$ reduces by 2 while current reduces by 4

Alternatively, V_{EFF} reduces by 2

=> random mismatch error increases by 2

...more unit devices are used, but overall area is maintained?

Smaller unit sizes allow use of common-centroid array structures

Area is the same

=> random mismatch error is the same

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What happens when...?

...W is increased by 4 (I_D is the same)? More area is used and V_{EFF} is reduced V_{EFF} decreases by 2, but σ_{VT} decreases by 2 => random mismatch error is the same

...W/L is increased by 2, while I_D and area are kept constant?

 V_{EFF} decreases by $\sqrt{2}$

=> random mismatch error increases by $\sqrt{2}$

Multi-bit Quantization

- ✓ Overcome stability-induced restrictions on NTF Larger no-overload range Dramatic improvements in SQNR
- ✓ Smaller step-size
 Less slewing, CT less sensitive to jitter
- ✓ Noise is 'whiter' Spurious tones can be avoided, dithering not required, design theory is much easier
- Increased complexity of flash ADC and DAC More comparators, more DAC switches, larger layout
- ★ Loses inherent linearity property of binary DACs DAC levels are not evenly spaced and are non-linear DAC errors are not noise shaped like ADC errors

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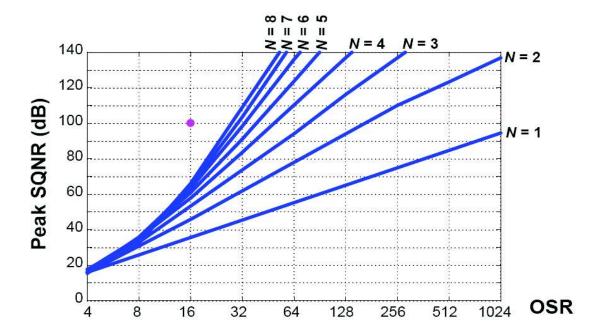
Multi-bit $\Delta\Sigma$

 Binary quantization imposes severe constraints on the NTF

Example: OSR = 16, a 5th-order binary modulator Binary quantizer only achieves SNR = 60dB With a 3-bit quantizer, SNR = 108dB is possible With a 4-bit quantizer, SNR = 120dB is possible

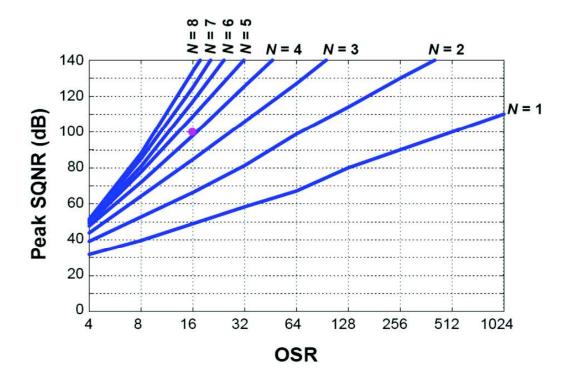
Compare SQNR for 1-bit and 3-bit $\Delta\Sigma$ modulators

SQNR Limits for 1-bit Modulators



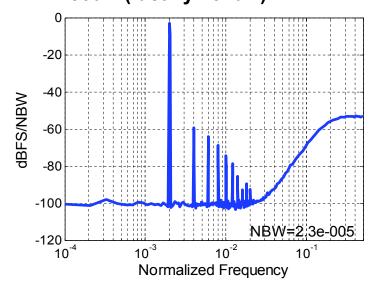
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SQNR Limits for 3-bit Modulators



DAC Mismatch

• 3rd-order, 3-bit quantizer, OSR=50 DAC cell mismatch σ = 1% SNDR = 50dB (ideally 107dB)



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DAC Mismatch

• Random DAC mismatches in multi-bit $\Delta\Sigma$ modulators are inevitable

DAC non-linearity causes harmonics that can limit the linearity of the whole modulator since they are introduced at the input

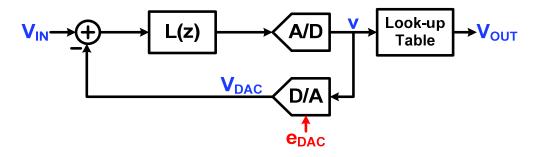
These errors can be overcome with digital techniques

Digital correction and calibration Mismatch shaping

Digital Correction

 Lookup table contains the equivalent of each DAC level

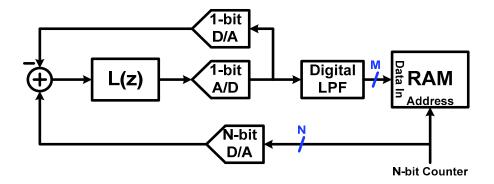
In practice, the look-up table only needs to store the differences between the actual and ideal DAC levels Look-up table calibrated so that $V_{OUT} = V_{DAC}$ => DAC errors are shaped by the loop



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Foreground Calibration

 Acquisition and storage of digital versions of DAC output signal (N-bit DAC, M-bit converter)
 Each of the 2^N DAC codes is held for 2^M clock periods With a 1-bit ΔΣ ADC, each DAC level is converted to its M-bit digital representation and stored in the RAM



For background calibration, see Silva, CICC '02

Mismatch Shaping

- Ensures that element mismatch error results in shaped 'noise'
- Operates without knowledge of the actual mismatch errors

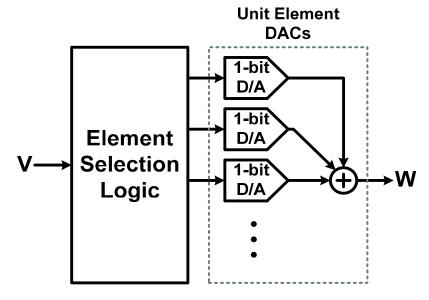
Even if the DAC errors drift, the output error will still be shaped

- Two requirements:
 - 1) Redundancy: There must be more than one way to create the same digital output (this is the case with thermometer coded outputs)
 - 2) Oversampling: Spectrally, there must be somewhere to put the unwanted mismatch noise

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Mismatch Shaping

 Element Selection Logic chooses when to use each of the DAC elements

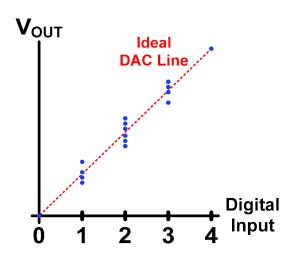


Mismatch Shaping

- Endpoints of DAC create ideal output curve Assumes no gain/offset error
- Average value of DAC codes lie on Ideal DAC Line

Errors are symmetric about the characteristic DAC line

Mismatch shaping chooses DAC cells to keep the error bounded



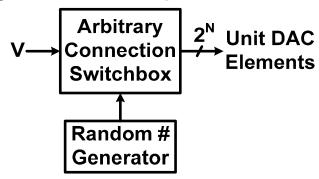
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Element Randomization

 Element selection logic randomly chooses DAC elements

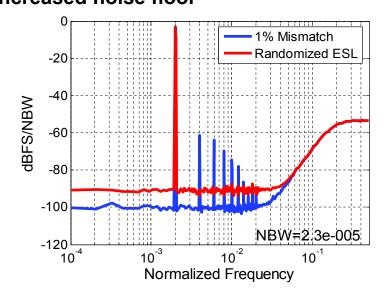
For each thermometer-coded input K, the ESL randomly chooses K unit DAC elements

DAC error is no longer correlated with the input Signal distortion is replaced by random noise spread throughout the entire spectrum



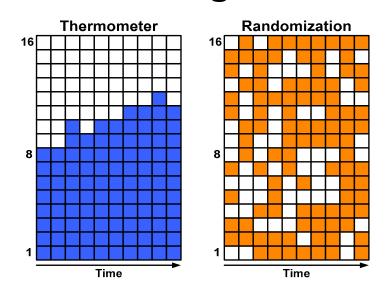
Element Randomization

SNDR = 62dB (improved from 50dB)
 Distortion no longer present
 Increased noise floor



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Element Usage Patterns

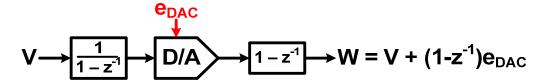


 Randomization: All DAC levels are used even when the input is almost constant

(Thermometer coded => no ESL is used)

Data-Weighted Averaging

- Data-directed element selection logic
- Conceptual system

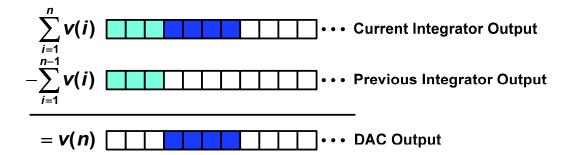


 DAC error is noise-shaped (high-pass filtered)
 But... DAC needs an infinite number of elements with the open-loop integrator

How can we implement this practically?

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Element Rotation

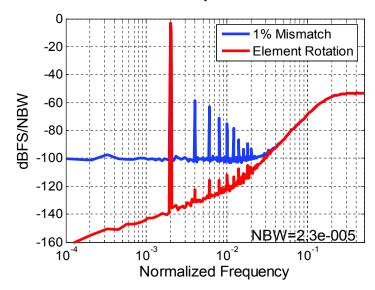


Use the elements in a circular fashion
 At time n, use the next v(n) elements in the array
 Loop back around when end of array is reached
 DAC error is noise shaped by desired 1-z-1 filter

DWA / Element Rotation

SNDR = 97dB (47dB improvement)

Noise floor is reduced since error is shaped Distortion is reduced (less correlated with input)



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Bidirectional DWA

DWA can cause tone generation if the DAC input is not a busy random signal

Like MOD1, if DAC input is DC/slowly varying, tones are produced since DAC output can be periodic

Bi-DWA

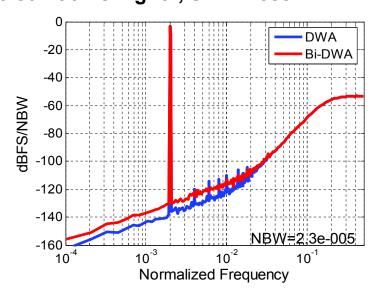
Element selection ping-pongs between two independent DWA algorithms, each rotating through DAC elements in opposite directions

Tends to reduce tonal behaviour, but also effectively decreases the OSR of the mismatch-shaping by a factor of 2

RMS mismatch noise increases by 9dB

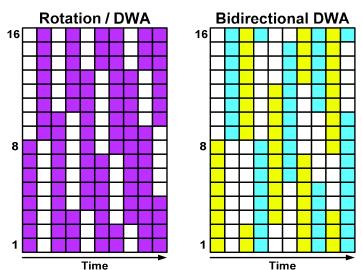
Bidirectional DWA

SNDR = 92dB (5dB worse than DWA)
 Distortion is reduced (less correlated with input)
 Noise floor is higher, SNDR less



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Element Usage Patterns



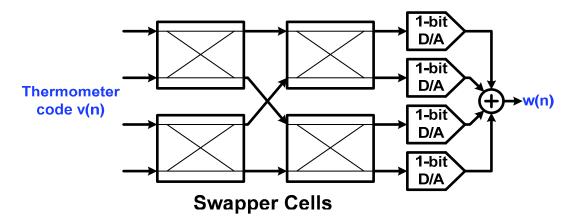
 Bidirectional DWA: same as two DWA schemes operating independently and in reverse directions on opposing clocks

Alternative Scheme: Swapping

 Each swapper tries to equalize the activity of its outputs [Adams, 1993]

Each element becomes a first-order noise-shaped sequence

Can be generalized to 2nd-order (Tree Structure)



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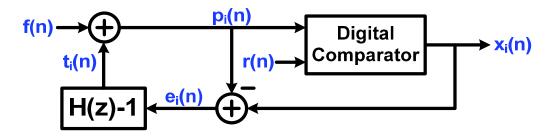
Vector-Based Mismatch Shaping

Achieves higher-order noise spectral shaping
 M digital noise-shaping loops for each unit element –
 an array of these loops make up the ESL

f(n) and r(n) are the same for all M loops

x_i(n) controls the corresponding DAC element

H(z) determines the order of the noise shaping



Vector-Based Mismatch Shaping

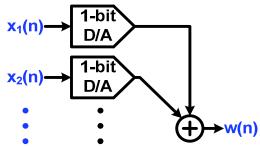
How is the output of the DAC noise shaped?

Output of the DAC elements $w(n) = \sum_{i=1}^{M} x_i(n)[1 + e_{DAC,i}]$

Loop filter outputs $X_i(n) = f(n) + [h * e_i](n)$

Resulting DAC element output is noise shaped by H where K is the intended DAC output

$$w(n) = K + h(n) * \sum_{i=1}^{M} [e_{DAC,i}e_{i}(n)]$$



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Vector-Based Mismatch Shaping

What are r(n) and f(n)?

r(n) and the digital comparators are not actually implemented – we need K outputs to be 1 so that w(n) is the correct value

The K largest $p_i(n)$ are quantized to $x_i(n)$ to minimize e_i(n), which reduces the DAC error

f(n) is chosen to keep the data in the loop positive, but also as small as possible => choose $f(n) = -\min_{i} [t_i(n)]$

What is H(z)?

H(z) is the NTF

For 1^{st} -order, $H(z) = 1 - z^{-1}$ (filter is z^{-1})

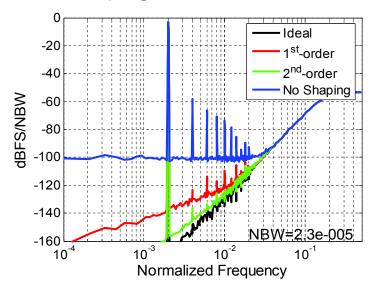
For 2^{nd} -order, $H(z) = (1 - z^{-1})^2$ (filter is $2z^{-1} - z^{-2}$)

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Vector-Based Shaping Spectrum

Ideal SNDR: 107dB, No shaping: 50dB

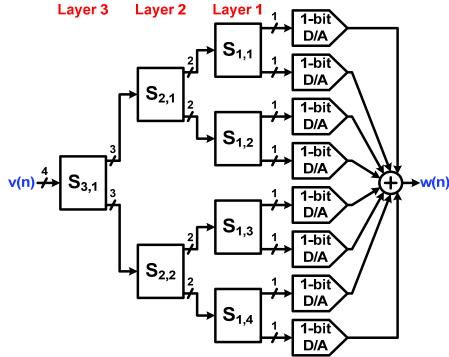
1st-order shaping: 97dB 2nd-order shaping: 105dB



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Tree Structure

Also useful for higher-order DAC noise-shaping



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Tree Structure

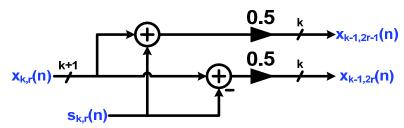
• Each switching block $S_{k,r}$ contains a unique sequence generator $s_{k,r}(n)$

k is the layer, r is the location within the layer

 $s_{k,r}(n)$ is a 1-bit sequence that determines the noise shaping of the structure

Final DAC mismatch noise will be a weighted sum of the s_k , sequences

Sample 1st-order bit sequence 1,0,...,0,-1,0,...,0,1,0,...



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Tree Structure

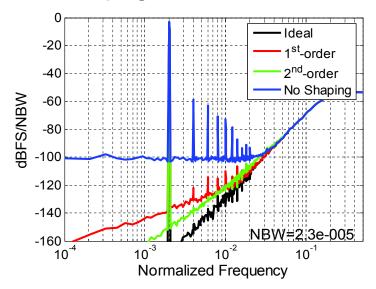
- Switching block must follow some rules
 - 1) The two outputs of each switching block must be between 0 and 2^{k-1}
 - 2) The sum of each switching block must equal the input
 - 3) Each $s_{k,r}(n)$ Lth-order shaped sequence must be uncorrelated from the $s_{k,r}(n)$ sequences of the other blocks

If these are satisfied, DAC noise will be an Lth-order shaped sequence [Galton, TCAS2 1997]

Tree Structure Spectrum

Ideal SNDR: 107dB, No shaping: 50dB

1st-order shaping: 97dB 2nd-order shaping: 100dB



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What You Learned Today

- 1. Mismatch sources
 Systematic, Random, Gradient
- 2. Matching techniques

 Common-centroid and interdigitation
- 3. Mismatch shaping schemes
 Randomization, Element Rotation, BiDWA, Swapping
 Vector-based, Tree Structure